

PSMN5R0-30YL

N-channel 30 V 5 m Ω logic level MOSFET in LFPAK

Rev. 4 — 9 March 2011

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- Class-D amplifiers
- DC-to-DC converters

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Table 1.	Quick reference du	Tital				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	-	30	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	91	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	61	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}$	-	3.63	5	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{see } \underline{\text{Figure } 14};$ $\text{see } \underline{\text{Figure } 15}$	-	3.8	-	nC



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{see } \underline{\text{Figure } 14}$	-	14.1	-	nC
Avalanche i	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 84 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped	-	-	32	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	D
3	S	source		
4	G	gate		<u></u>
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R0-30YL	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V_{DSM}	peak drain-source voltage	$t_p \le 25 \text{ ns}$; f $\le 500 \text{ kHz}$; $E_{DS(AL)} \le 130 \text{ nJ}$; pulsed	-	35	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	64	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	91	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; see Figure 3	-	336	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	61	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	84	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$	-	336	Α
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 84 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped	-	32	mJ

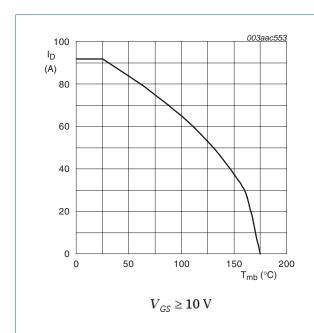
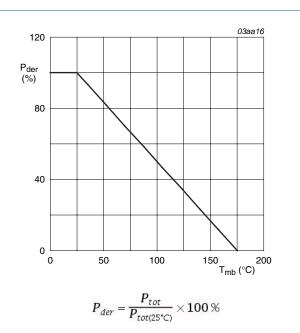
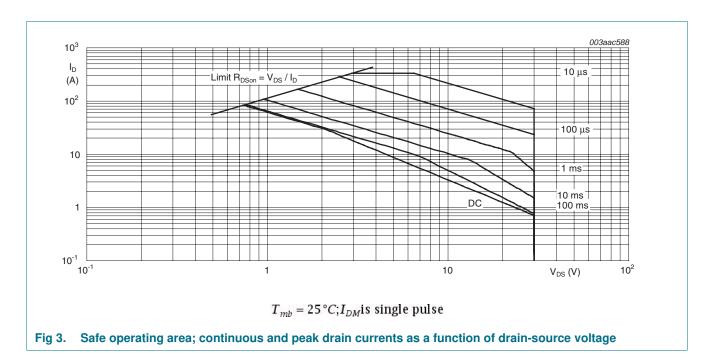


Fig 1. Continuous drain current as a function of mounting base temperature



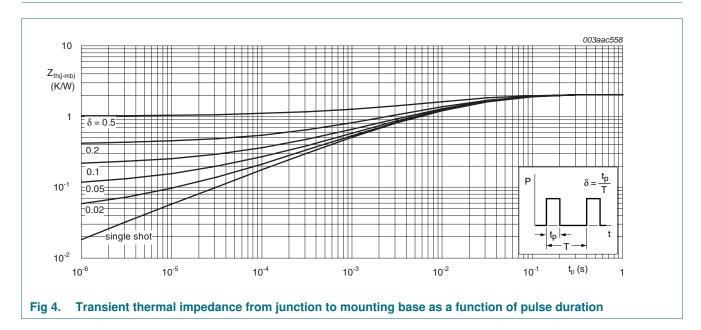
g 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1.39	2	K/W



6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 150 °C; see Figure 12	0.65	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 12	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	5.08	6.7	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 13	-	-	8.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	3.63	5	mΩ
R_G	gate resistance	f = 1 MHz	-	0.69	1.5	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14	-	14.1	-	nC
		$I_D = 10 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	29	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	27	-	nC
Q_{GS}	gate-source charge	$I_D = 10 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 4.5 \text{ V}$;	-	4.3	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	1.4	-	nC
Q_{GD}	gate-drain charge		-	3.8	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.5	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1760	-	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	373	-	pF
C _{rss}	reverse transfer capacitance		-	171	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	19	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	35	-	ns
t _{d(off)}	turn-off delay time		-	29	-	ns
t _f	fall time		-	12	-	ns

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 Table 6.
 Characteristics ... continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.84	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu s$; $V_{GS} = 0 \text{ V}$;	-	30	-	ns
Q _r	recovered charge	$V_{DS} = 20 \text{ V}$	-	21	-	nC

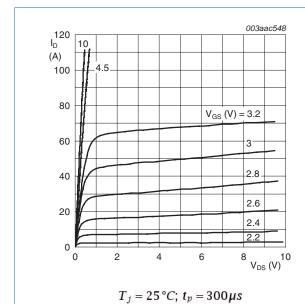
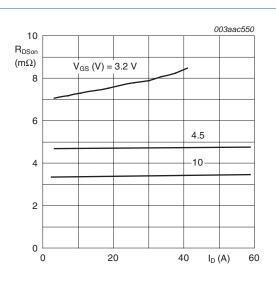


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_j = 25 \,^{\circ}C; t_p = 300 \,\mu s$$

Fig 6. Drain-source on-state resistance as a function of drain current; typical values

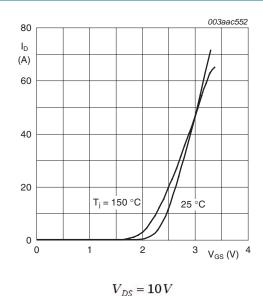
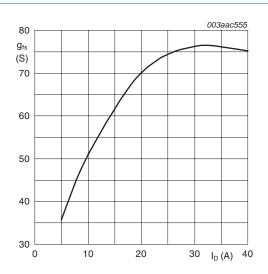


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 15 V$

Fig 8. Forward transconductance as a function of drain current; typical values

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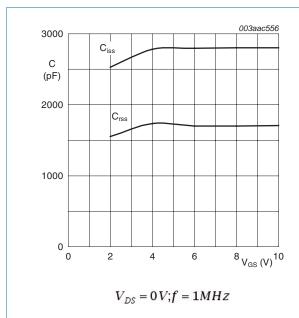


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

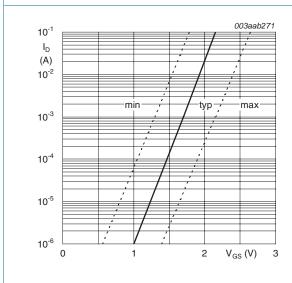
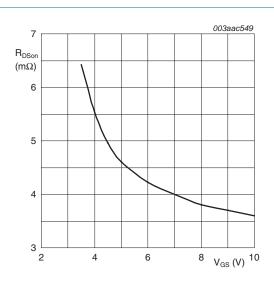


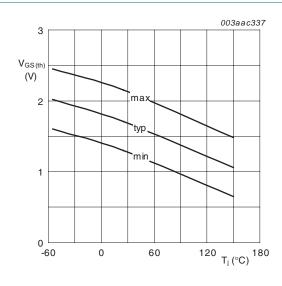
Fig 11. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$



 $T_j = 25 \,^{\circ}C; I_D = 15A$

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 12. Gate-source threshold voltage as a function of junction temperature

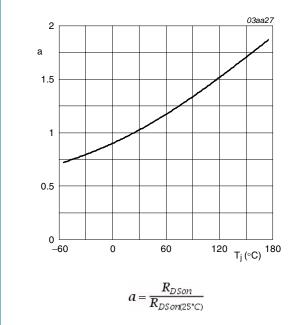


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

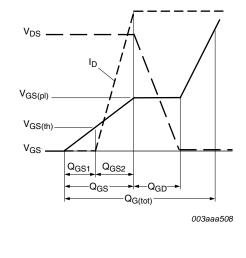


Fig 14. Gate charge waveform definitions

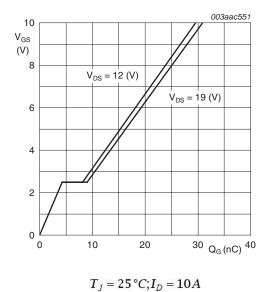


Fig 15. Gate-source voltage as a function of gate

charge; typical values

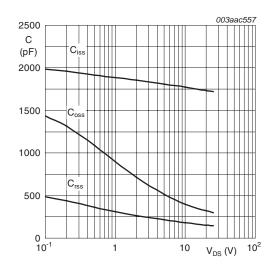


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $V_{GS} = 0V; f = 1MHz$

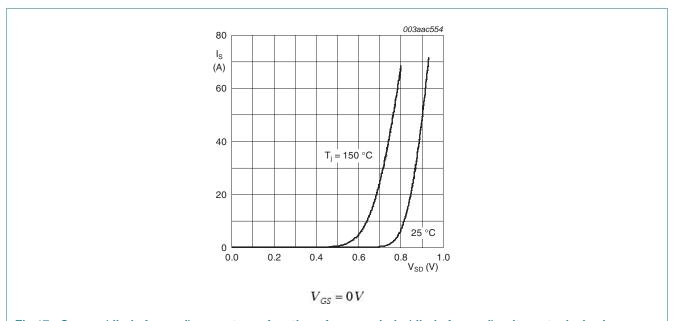


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads **SOT669** С c₂- E_1 mounting b₄ base D_1 D Х **→** w M A е 1/2 e (A_3) С detail X 5 mm scale **DIMENSIONS (mm are the original dimensions)** D₁⁽¹⁾ A₂ b_3 D⁽¹⁾ E⁽¹⁾ UNIT Α b b_2 b_4 E₁⁽¹⁾ L_2 θ Α₁ A₃ С c_2 е L_1 у 1.20 0.15 1.10 0.50 4.41 0.9 0.25 0.30 4.10 3.3 6.2 0.85 1.3 0.25 0.00 0.95 0.35 3.62 2.0 0.7 0.19 0.24 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

Fig 18. Package outline SOT669 (LFPAK)

IEC

OUTLINE

VERSION

SOT669

PSMN5R0-30YL

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JEITA

REFERENCES

JEDEC

MO-235

ISSUE DATE

04-10-13

06-03-16

EUROPEAN

PROJECTION

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN5R0-30YL v.4	20110309	Product data sheet	-	PSMN5R0-30YL_3
Modifications:	 Various changes 	to content.		
PSMN5R0-30YL_3	20100104	Product data sheet	-	PSMN5R0-30YL_2

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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